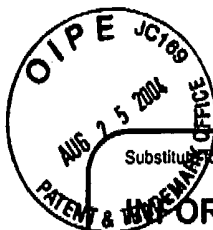


PTO/SB/08a (08-03)



PTO/SB/08b(08-03)

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Sheet 2 of 3

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Application Number	09/922,426
Filing Date	August 3, 2001
First Named Inventor	Trulson et al.
Art Unit	1639
Examiner Name	Maurio Garcia-Baker CELSA
Attorney Docket Number	3305.1

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
MA	8	Griffing and West IEEE Electron Device Letters EDL-4(1): 14(1983).	
ML	9	GHANDI, VLSI Fabrication Principles, 1983, Chapter 10.	
ML	10	HOFFER et al., Contrast enhanced uv lithography with polysilanes, Advances in Resist Technology, 1984, 108-16, SPIE Vol. 469.	
ML	11	HALLE, L., et al., J. Vac. Sci. Technol. B., 1985, 323-326, Vol. 3(1).	
ML	12	SHEATS, et al., SPIE Proc. 1986, 631, 171	
ML	13	UCHINE, et al., Proc. Poly. Mat. Sci. And Eng., 1986, 55, 604-607.	
ML	14	PAUL R. WEST, et al., Contrast Enhanced Photolithography: Application of Photobleaching Processes in Microlithography, J. Imaging Science, March/April 1986, 65-68, Vol. 30, No. 2.	
ML	15	DON R. STROM, Optical Lithography and Contrast Enhancement, Semiconductor International, May 1986, 162-67.	
ML	16	ENDO, et al., High aspect-ratio resist pattern fabrication by alkaline surface treatment, J. Vac. Sci. Technol. B., 1988, 1076-79, Vol. 7(5).	
ML	17	UCHINO, SHOU-ICHI et al., Synthesis of new metal-free diazonium salts and their applications to microlithography, Journal of Photopolymer Science and Technology (1989); 2 (1): 255-299.	
ML	18	REISER, et al., Photoreactive Polymers: the Science and technology of Resists, 1989, 226-29.	

Examiner  
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<i>MC</i>	19	SALAMY, et al., Proc. Electrochem. Soc., 1989, 90:36.	
<i>PL</i>	20	DURAND, et al., Nucleic Acids Res., 1990, 8353-59, Vol 18., No. 21.	
<i>PL</i>	21	TOSHIHIKO TANAKA, et al., Sub-Halfmicron Lithography Using a High-Contrast I-Line CEL, Japanese J. Applied Physics, Sept. 1990, 1860-61, Vol. 29, No. 1.	
<i>PL</i>	22	R. PFORR, et al., Contrast enhancement of the resist latent image using exposure induced absorption amplification - fundamental, modeling, and applicability, Microelectronic Engineering, 1992, 321-328, Vol. 17.	
<i>PL</i>	23	DAVID M. TEEGARDEN, et al., Contrast Enhancement Lithography System Based on Pyrylium Dye Bleach Chemistry, J. Imaging Science and Technology, 1993, 149-155, Vol. 37, No. 2.	
<i>PL</i>	24	THOMPSON, L.F., et al., Introduction to Microlithography, America Chemical Society, 1994 212-232.	
<i>PL</i>	25	HUANG, Proc. SPIE - Int. Soc. Opt. Eng., 1999, 3678, (Pt. 2) 340-51.	
Examiner Signature	<i>[Signature]</i>		Date Considered <i>11/3/04</i>

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